



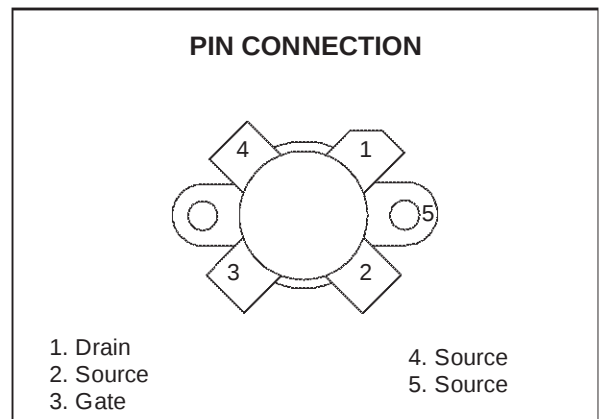
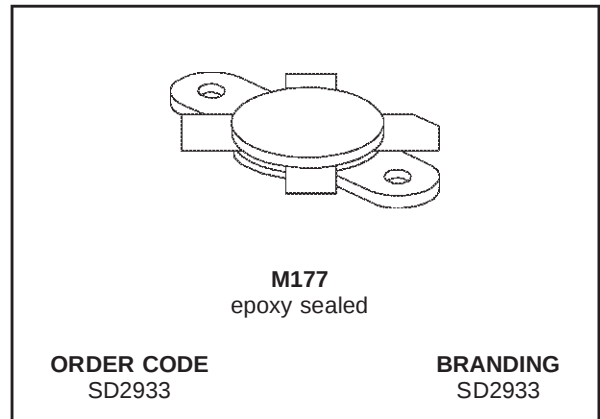
SD2933

RF POWER TRANSISTORS HF/VHF/UHF N-CHANNEL MOSFETs

- GOLD METALLIZATION
- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION
- $P_{OUT} = 300\text{ W MIN. WITH } 20\text{ dB GAIN @ } 30\text{ MHz}$
- THERMALLY ENHANCED PACKAGING FOR LOWER JUNCTION TEMPERATURES

DESCRIPTION

The SD2933 is a gold metallized N-Channel MOS field-effect RF power transistor. It is intended for use in 50 V dc large signal applications up 150 MHz. It's special low thermal resistance package, makes it ideal for ISM applications where reliability and ruggedness are critical factors.



ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain Source Voltage	125	V
V_{DGR}	Drain-Gate Voltage ($R_{GS} = 1\text{M}\Omega$)	125	V
V_{GS}	Gate-Source Volatge	± 20	V
I_D	Drain Current	40	A
P_{DISS}	Power Dissipation	648	W
T_j	Max. Operating Junction Temperature	200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{th(j-c)}$	Junction -Case Thermal Resistance	0.27	$^{\circ}\text{C/W}$
$R_{th(c-s)}$	Case-Heatsink Thermal Resistance*	0.15	$^{\circ}\text{C/W}$

* Determined using a flat aluminum or copper heatsink with thermal compound applied (Dow Corning 340 or equivalent).

ELECTRICAL SPECIFICATION (T_{CASE} = 25°C)

STATIC

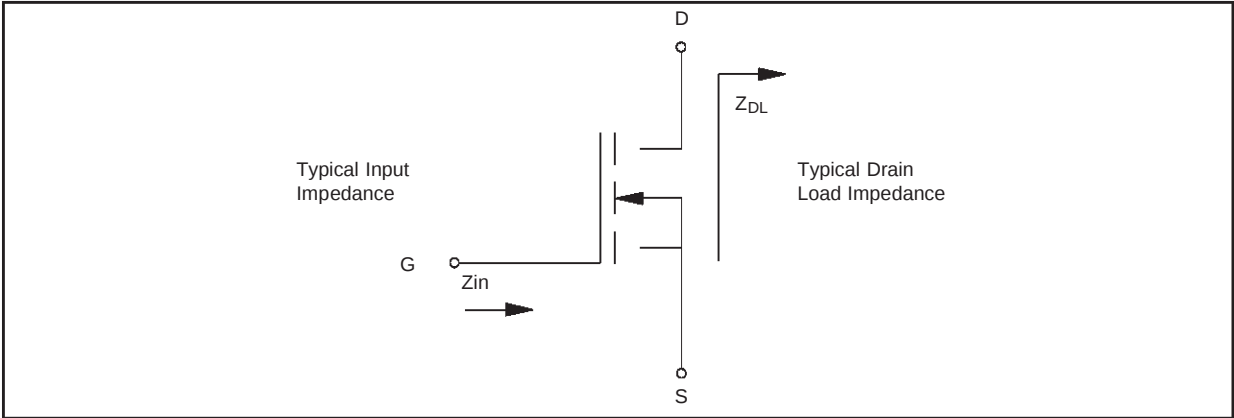
Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V _{(BR)DSS}	V _{GS} = 0 V	I _{DS} = 200 mA	125			V
I _{DSS}	V _{GS} = 0 V	V _{DS} = 50 V			10	mA
I _{GSS}	V _{GS} = 20 V	V _{DS} = 0 V			10	μA
V _{GS(Q)}	V _{DS} = 10 V	I _D = 250 mA	1.5		4	V
V _{DS(ON)}	V _{GS} = 10 V	I _D = 10 A			3	V
G _{FS}	V _{DS} = 10 V	I _D = 10 A	10			mho
C _{ISS}	V _{GS} = 0 V	V _{DS} = 50 V		1000		pF
C _{OSS}	V _{GS} = 0 V	V _{DS} = 50 V		372		pF
C _{RSS}	V _{GS} = 0 V	V _{DS} = 50 V		29		pF

REF. 7170198D

DYNAMIC

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
P _{OUT}	V _{DD} = 50 V	I _{DQ} = 250 mA f = 30 MHz	300	400		W
G _{PS}	V _{DD} = 50 V	I _{DQ} = 250 mA P _{OUT} = 300 W f = 30 MHz	20	23.5		dB
η _D	V _{DD} = 50 V	I _{DQ} = 250 mA P _{OUT} = 300 W f = 30 MHz	50	65		%
Load Mismatch	V _{DD} = 50 V I _{DQ} = 250 mA P _{OUT} = 300 W f = 30 MHz All Phase Angles		3:1			VSWR

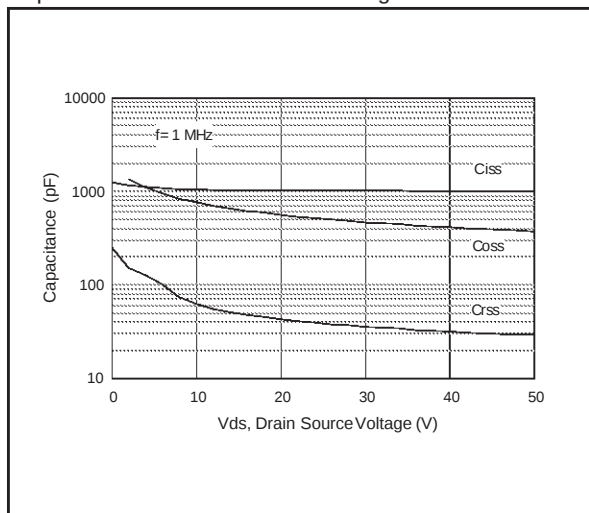
IMPEDANCE DATA



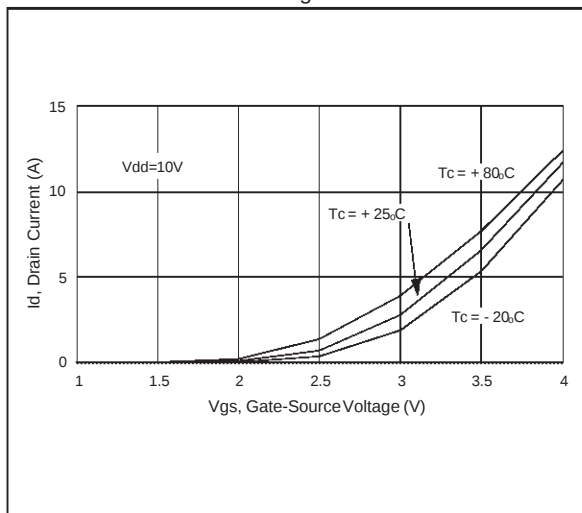
FREQ	Z _{IN} (Ω)	Z _{DL} (Ω)
30 MHz	1.8 - j 0.2	6.8 + j 2.3
108 MHz	1.9 + j 0.2	1.6 + j 1.4
175 MHz	1.9 + j 0.3	1.5 + j 1.6

TYPICAL PERFORMANCE

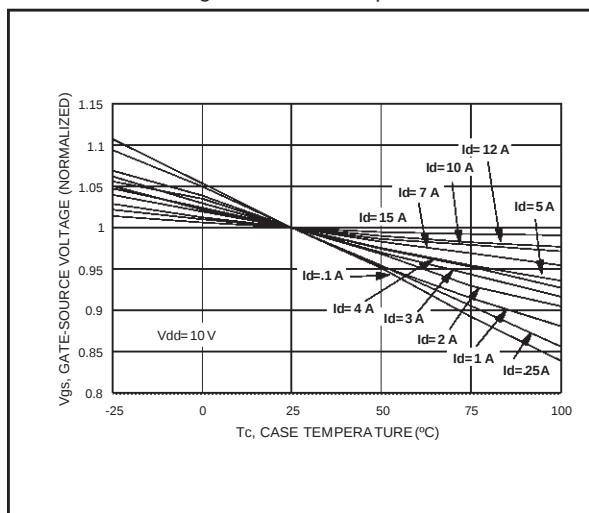
Capacitance vs. Drain-Source Voltage



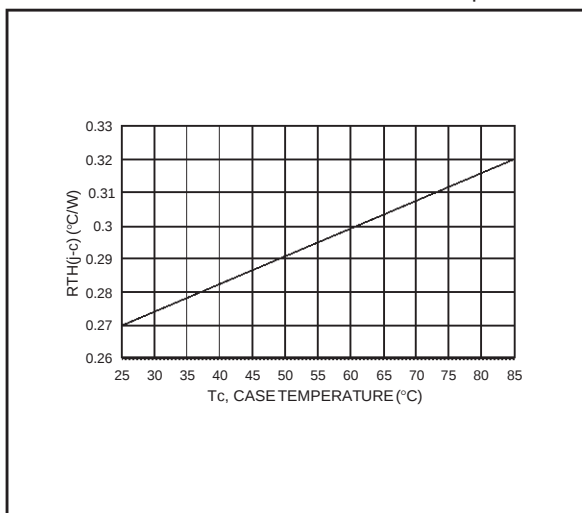
Drain Current vs. Gate Voltage



Gate-Source Voltage vs. Case Temperature

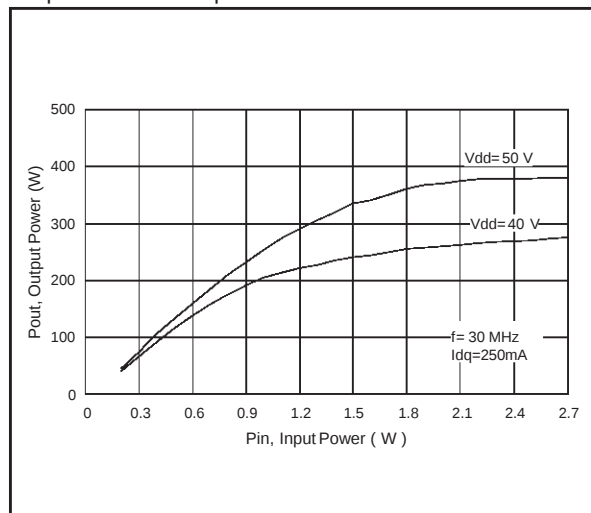


Maximum Thermal Resistance vs. Case Temperature

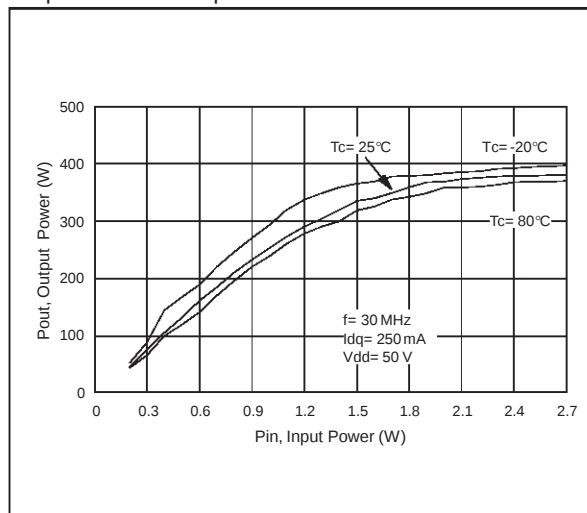


TYPICAL PERFORMANCE

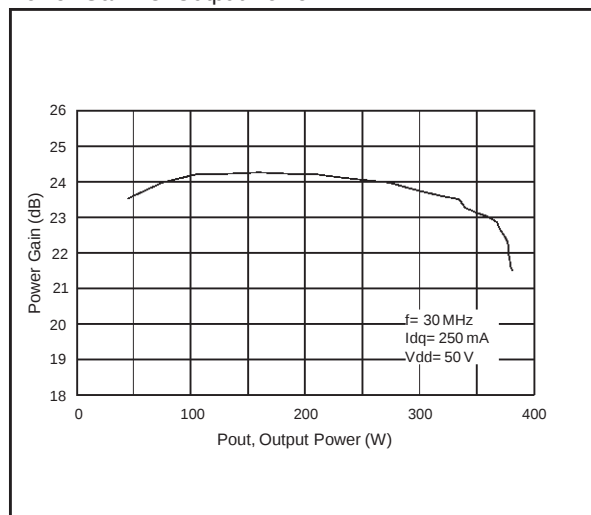
Output Power vs. Input Power



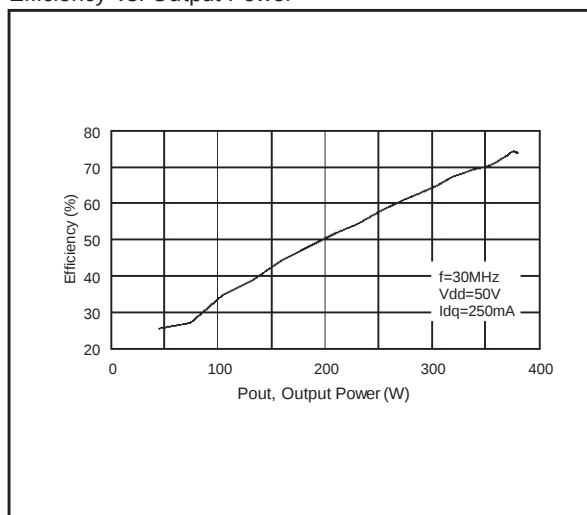
Output Power vs. Input Power



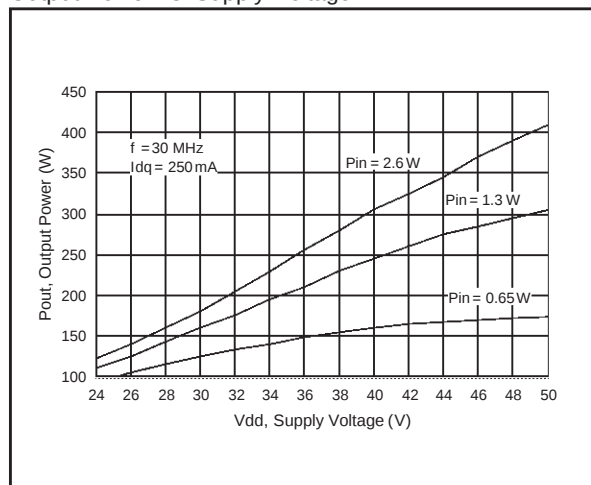
Power Gain vs. Output Power



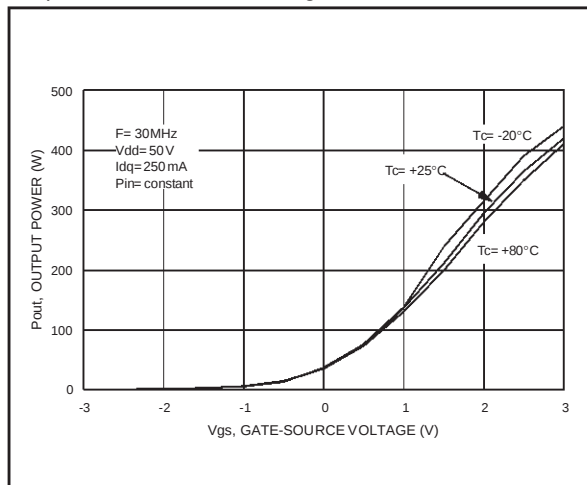
Efficiency vs. Output Power



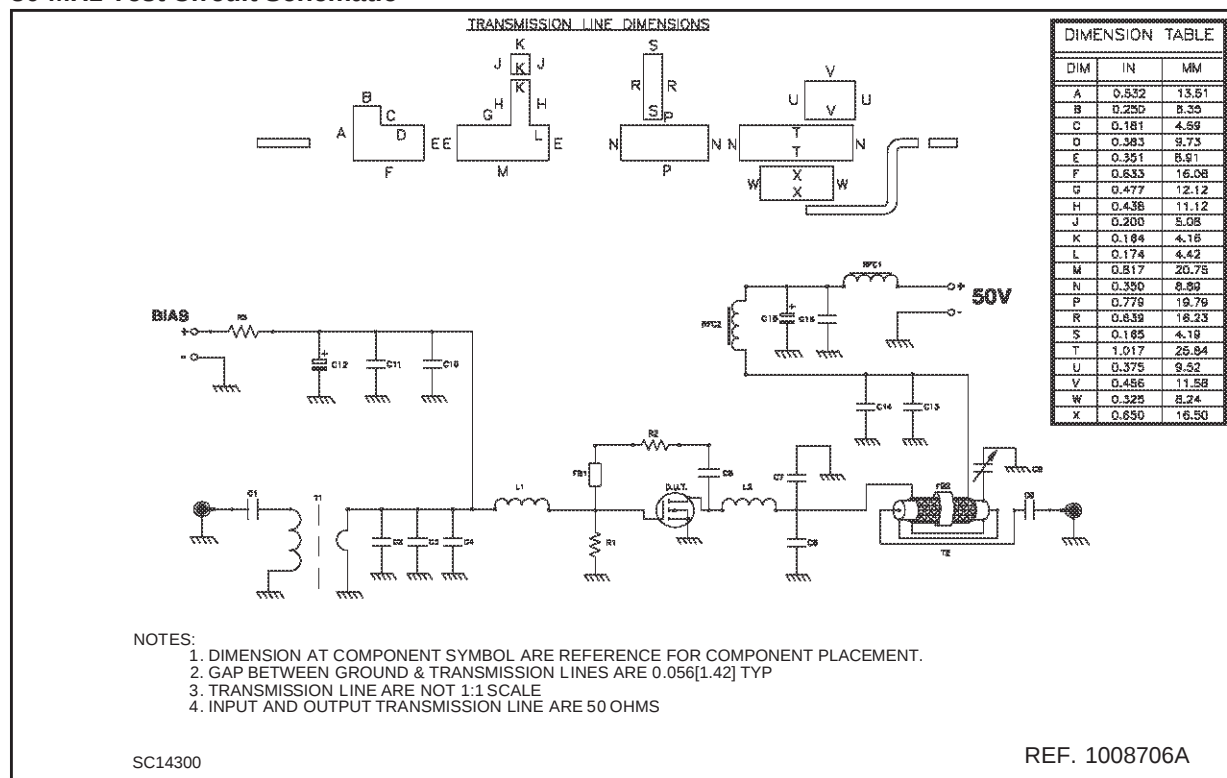
Output Power vs. Supply Voltage



Output Power vs. Gate Voltage



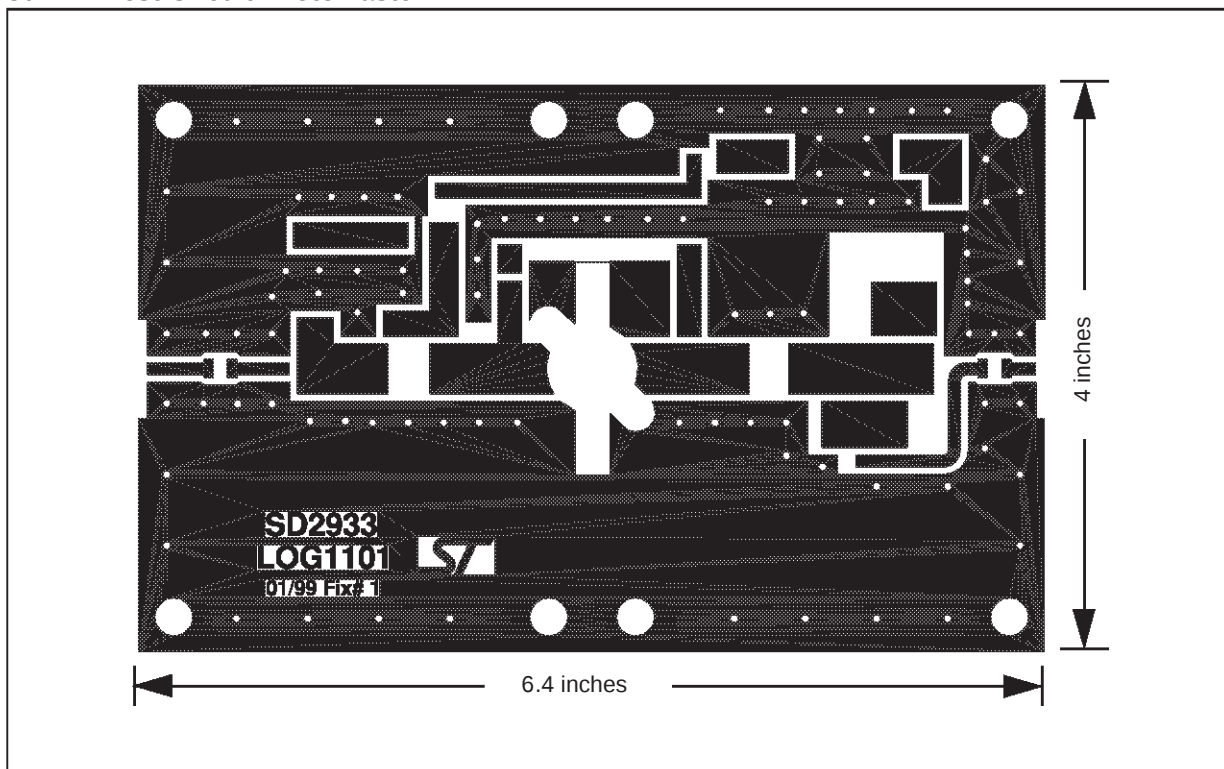
30 MHz Test Circuit Schematic



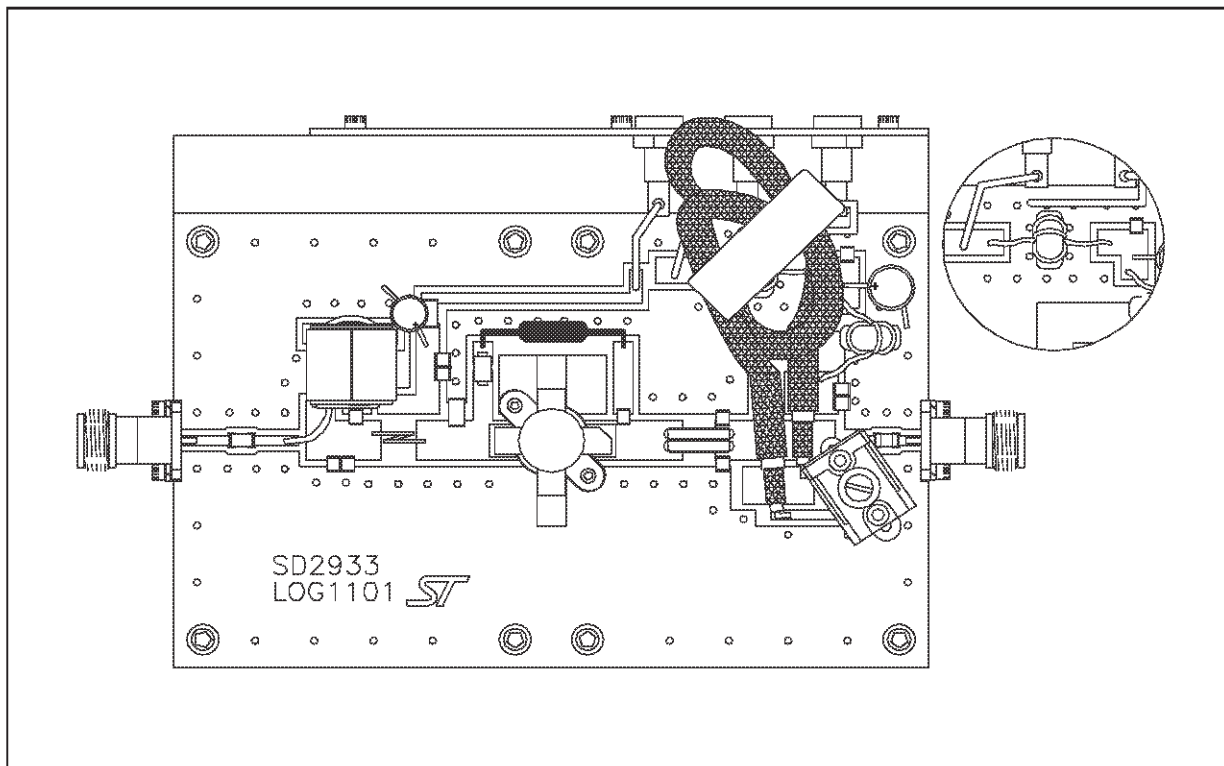
30 MHz Test Circuit Component Part List

C1,C9	0.01 μ F / 500 V SURFACE MOUNT CERAMIC CHIP CAPACITOR
C2, C3	750 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C4	300 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C5,C10,C11,C14,C16	10000 pF ATC 200B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C6	510 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C7	300 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C8	175-680 pF TYPE 46 STANDARD TRIMMER CAPACITOR
C12	47 μ F / 63 V ALUMINUM ELECTROLYTIC RADIAL LEAD CAPACITOR
C13	1200 pF ATC 700B SURFACE MOUNT CERAMIC CHIP CAPACITOR
C15	100 μ F / 63 V ALUMINUM ELECTROLYTIC RADIAL LEAD CAPACITOR
R1,R3	1 K OHM 1 W SURFACE MOUNT CHIP RESISTOR
R2	560 OHM 2 W WIRE-WOUND AXIAL LEAD RESISTOR
T1	HF 2-30 MHz SURFACE MOUNT 9:1 TRANSFORMER
T2	RG - 142B/U 50 OHM COAXIAL CABLE OD = 0.165[4.18] L 15"[381.00] COVERED WITH 15"[381.00] TINNED COPPER TUBULAR BRAND 13/65" [5.1] WIDTH
L1	1 3/4 TURN AIR-WOUND 16 AWG ID = 0.219 [5.56] POLY-COATED MAGNET WIRE
L2	1 3/4 TURN AIR-WOUND 12 AWG ID = 0.250 [6.34] BUS BAR WIRE
RFC1,RFC2	3 TURNS 14 AWG WIRE THROUGH FAIR RITE TOROID
FB1	SURFACE MOUNT EMI SHIELD BEAD
FB2	TOROID
PCB	ULTRALAM 2000. 0.030" THK, ϵ_r = 2.55, 2 Oz ED CU BOTH SIDES

30 MHz Test Circuit Photomaster

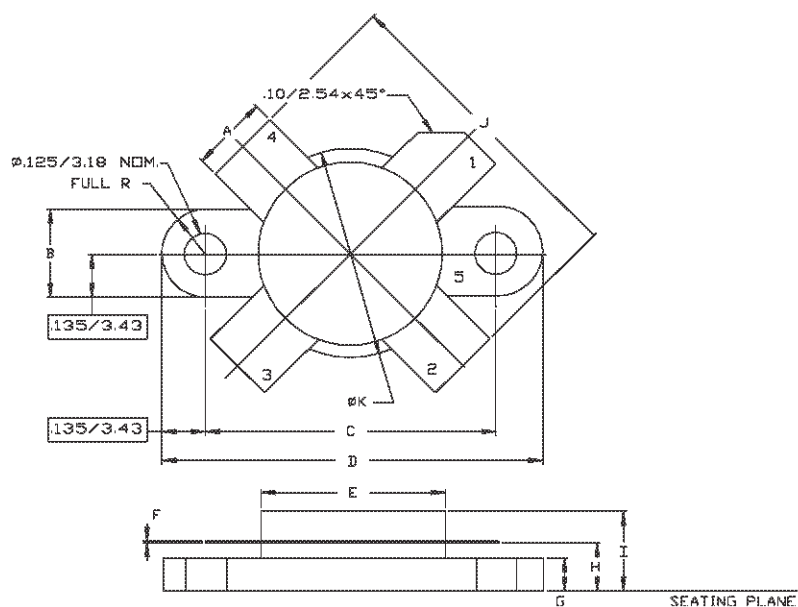


30 MHz Test Circuit



M177 (.550 DIA 4/L N/HERM W/FLG) MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A	5.72		5.97	0.225		0.235
B	6.73		6.96	0.265		0.275
C	21.84		22.10	0.860		0.870
D	28.70		28.96	1.130		1.140
E	13.84		14.10	0.545		0.555
F	0.08		0.18	0.003		0.007
G	2.49		2.74	0.098		0.108
H	3.81		4.32	0.150		0.170
I			7.11			0.280
J	27.43		28.45	1.080		1.120
K	15.88		16.13	0.625		0.635



Controlling Dimension: Inches

1011012D

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